

The technology to improve tunnnel diode rectification performance

Introducing a nanoparticle layer into MIM tunnel diodes to significantly improve rectification performance!

Overview

- Metal/insulator/metal tunnel diodes (MIM tunnel diodes) are used when rectifying signals of frequencies in <u>the</u> <u>infrared and terahertz regions</u>.
- However, it is difficult to improve the rectification performance because <u>there is a trade-off between</u> <u>electrical resistance and asymmetry.</u>
- The invention has solved the above issue <u>by introducing</u> <u>metallic nanoparticle layers (NPs)</u> into the MIM tunnel diodes and changing <u>the tunnel barrier at forward and backward biases</u> by the effect of electric field concentration.
- Since the invention has <u>greatly improved rectifying</u> <u>performance</u> compared to tunnel diodes without NPs, the present tunnel diodes can be expected to be used to <u>high-frequency devices (Optical rectenna, IR, THz</u> <u>detector)</u>.

Product Application

- Optical rectenna
- IR, THz detecter

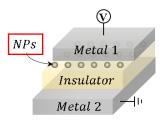
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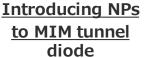
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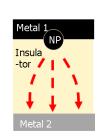
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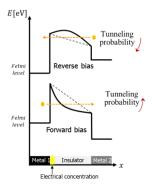
Features · Outstandings





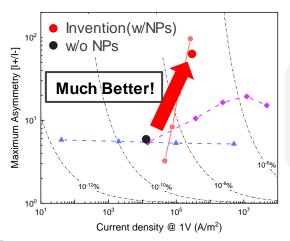


Electric field concentration



<u>Tunnel barrier</u> <u>Changes</u>

⇒ Improve asymmetry



Asymmetry

⇒ 10 Times!

Current density

⇒ 20 Times!

Related Works

[1] Zen Liu, Shunsuke Abe, Makoto Shimizu, Hiroo Yugami *Appl. Phys. Lett.* **122**, 093502 (2023)

Contact



I. Phys. Lett. **122**, 093502 (2023)